Diffraction techniques in the Scanning Electron Microscope (SEM)

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Scanning electron microscopy (SEM)







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Scattering and diffraction



Electron Diffraction Techniques in the SEM

1. ECCI – Electron channelling contrast images Dislocations in nitride thin films

Observation of crystal defects (dislocation, stacking faults and grain boundaries)

2. EBSD - Electron Backscatter Diffraction

Microstructural – crystallographic characterization technique for <u>bulk</u> <u>samples</u>



C. Trager-Cowan: http://ssd.phys.strath.ac.uk/index.php/Elec tron_channeling_contrast_imaging



Fe3% Si



3. TKD - Transmission Kikuchi Diffraction

Microstructural – crystallographic characterization technique for <u>thin</u> <u>samples</u>







EBSD Electron Backscatter Diffraction



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Electron backscatter diffraction - history

- 1928 First observation of BKP by Nishikawa& Kikuchi
- 1973 Observation of BKP in a SEM by Venables and Harland
- 1984 <u>Dingley</u> started using TV camera and computer software for orientation determination
- 1992- Introduction of the Hough transform by Krieger Lassen et al.
- 1993 Introduction of OIM (Orientation image microscopy) by Adams et al.





Formation of Kikuchi pattern – step 1

The formation of EBSD patterns is a <u>two-step process</u>

POINT SOURCE

• Electrons strike the specimen

1. They are then inelastic scattered from the point source in all directions

<u>Inelastic:</u> some loss of energy



Formation of Kikuchi pattern – step 2

2. *crystalline materials: those* electrons (from inside the point source) are diffracted by the crystal lattice planes when <u>the Bragg condition is satisfied</u>

Bragg equation: $n\lambda = 2d \sin \theta$

λ: wavelength of the electrons
d : spacing of the crystal planes
n: is an interger
θ : angle of incidence



2 lattice plane



Simplified illustration – one electron and one lattice plane

 Since the <u>scattered electrons</u> are travelling in <u>all</u> <u>direction</u>, the diffracted beam will lie on one of <u>two cones</u>.

Thin sample



Oxford instrument

Detector screen



Adapted from: Ref.:http://ssd.phys.strath.ac.uk/index.php/Electron_backscatter_diffraction_(EBSD)

Two electron and two lattice plane



Adapted from: Ref.:http://ssd.phys.strath.ac.uk/index.php/Electron_backscatter_diffraction_(EBSD)



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Simplified illustration – one electron and one lattice plane



Ref.:http://ssd.phys.strath.ac.uk/index.php/Electron_backscatter_diffraction_(EBSD)

EBSD – tilted sample

Bulk sample

EBSD detector

Tilt the sample to approximately 70° (best compromise between intensity and resolution)



EBSD – tilted sample

Scattering from single lattice planes



EBSD patterns



Position of bands <u>directly linked</u> to the crystallographic orientation

Diffraction from a specific lattice plane

Intersections of bands = intersections of planes = zone axes

Ti-Al 20kV *Ref.: Dr. Emmanuelle Boehm Courjault;* Introduction to EBSD (Electron BackScatter Diffraction) :Principle and Applications

Angles between bands = angles between planes

EBSD patterns are:

- <u>unique</u> for a specific crystal orientation
- is controlled by the crystal structure: space group symmetry, lattice parameters, *precise* composition



Surface sensitive technique

- Although EBSPs are created by <u>backscattered</u> <u>electrons</u>, the signal does not come from the whole BSE interaction volume
- Instead, the diffraction signal originates from a "POINT SOURCE" \rightarrow 5-10nm under the surface







Surface sensitive technique

- The top layer
 - Free from damage
 - Free from contamination
 - or oxidation layers
 - in case of non conductive samples
 → the <u>coat</u> must be kept very thin –
 typically in the range of <u>2-5 nm</u>.
- Due to high tilt angles (typically 70°),
 - <u>surface topography</u> must be kept to an absolute <u>minimum</u>.



Sample strongly tilted – Resolution y axis is 3x worst



Signal intensity



From: S. Baeck, TSL tutorial S. Wright Raw pattern Only a small fraction of the electron arriving at the phosphor screen are diffracted

Background intensity supresses both the contrast and sharpness.

Background



Nb-pattern from S. Zaefferer



Signal is material dependent

Increasing atomic number (↑ Z):

- Increase the amount of backscatter electrons <u>Pattern quality</u>
- Decreases the interaction volume improve spatial resolution





Short take home message

- It is not easy to prepare the sample for EBSD
- Once you get patterns, it runs fully automated

Automate data acquisition, pattern indexing and orientation determination

In one automate run you get:

- Grain size,
- texture,
- grain boundary distribution,
- phase distribution,
- ...



Choose the step size and the area





Runs very fast: Now a days up to **3000** patterns per seconds

Automated indexing during the acquisition



Orientation map



Grains size distribution

Grain boundary map



Misorientation angles

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23	0	23	8	-6.249	0	0	0	0	0	8	-1	
24	0	24	0	-6.528	5 0	0	9	9	0	0	-1	
25	0	25	e	-6.792	5 0	0	0	0	0	0	-1	
26	0	26	0	-7.864	2.0	0	0	0	0	0	-1	
27	0	27	0	-7.335	9.9	0	0	0		8	-1	
28	0	28	8	+7.687	6.0		0	8		0	-1	
29	0	29		-7.879	3 0	0	0	0	0		-1	
30	0	30	0	-8.151	0	0	0	0	0	8	-1	
31	0	31	8	-8.422	7.0	8	9	8	0	8	-1	
32	0	32	0	-8.694		0	0	0		0	-1	
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10	9	41		-1.115					0	0		1.2
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Colourful image





1111

Orientation with respect to the sample coordinate system

Z-direction

Y-direction



Χ











Adapted from: Channel 5 User Manual, HKL Technology A/S, Hobro, Denmark (2001).

EBSD is a materials characterization tool





Application example -1

DTU Nanolab

Niobium deformed by ECAP and heat treated for 15 min



Local misorientation map



Orientation bands – related to the type of deformation - **shear**



Deformed areas



Recrystallized areas

		Total	Partition
Min	Max	Fraction	Fraction
0	3	0.999	0.999

H. Sandim; www.imim.pl



15 um